

Features:

- Current transfer ratio (CTR:MIN.50% at IF =5mA, VCE =5V)
- High isolation voltage between input and output (Viso=5000 V rms)
- Compact dual-in-line package EL817*:1-channel type
- Pb free
- UL approved (No. E214129)
- VDE approved (No. 132249)
- SEMKO approved (No. 300858,300859,304855, 304827,2022251,0143133/01-03,0101083/01, 303345,303349)
- NEMKO approved (No. P04203585, P00102385, P02101854)
- DEMKO approved (No. 311822-01/02/03,310352-01, 311822-03A)
- CSA approved (No. 1143601)
- BSI approved (No. 8592, 8593)
- Options available:
 - Leads with 0.4"(10.16mm) spacing (M Type)
 - Leads bends for surface mounting (S and S1 Type)
 - Tape and Reel of Type I for SMD(Add"-TA" Suffix)
 - Tape and Reel of Type **II** for SMD(Add"-TB" Suffix)
 - The tape is 16mm and is wound on a 33cm reel
- The product itself will remain within RoHS compliant version.

Description

The EL817 series contains a infrared emitting diode optically coupled to a phototransistor. It is packaged in a 4-pin DIP package and available in wide-lead spacing and SMD option.

Applications

- Computer terminals
- System appliances, measuring instruments
- Registers, copiers, automatic vending machines
- Electric home appliances, such as fan heaters, etc.
- Signal transmission between circuits of different potentials and impedances



EL817



EL817M



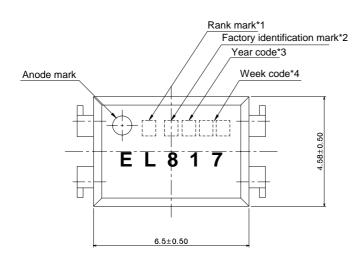
EL817S

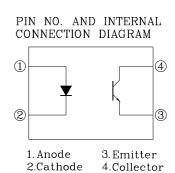


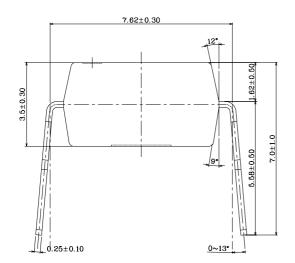
Device Selection Guide

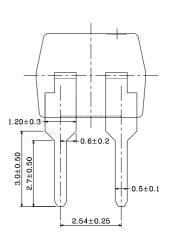
Part. No.	Chip Material		
	IR	PT	
EL817*	GaAs	Silicon	

Package Dimensions





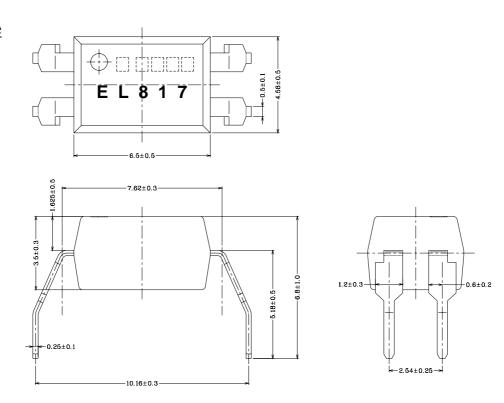




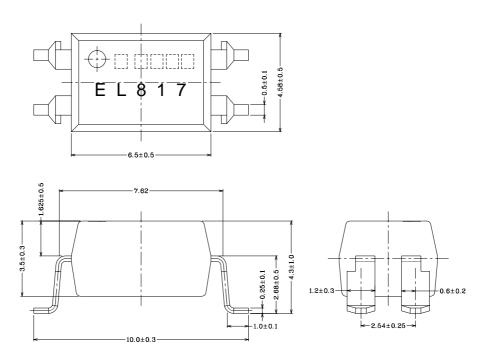


Package Dimensions

M Type

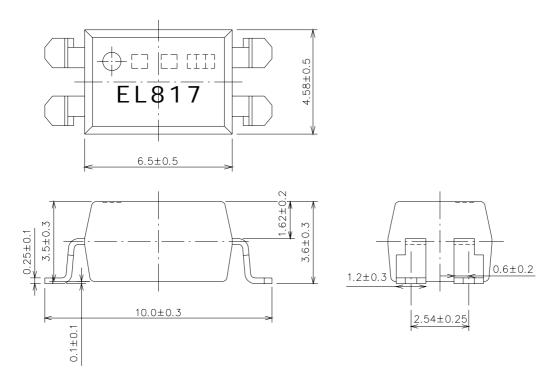


S Type





S1 Type



Notes:

- 1. Rank shall be or shall not be marked
- 2. Factory code shall be marked (T: Taiwan / C: China)
- 3. Year date code
- 4. 2-digit work week
- 5. All dimensions are in millimeters
- 6. Specifications are subject to change without notice



Absolute Maximum Ratings

 $(Ta=25^{\circ}C)$

Parameter		Symbol	Rating	Unit
Forward Current		I_{F}	50	mA
Input	Reverse Voltage	V_R	6	V
	Power Dissipation	P	70	mW
	Collector Power Dissipation		150	mW
Output	Collector Current	I_{C}	50	mA
	Collector-Emitter Voltage	V_{CEO}	35	V
	Emitter-Collector Voltage	V_{ECO}	6	V
To	Total Power Dissipation		200	mW
*1 Isolation Voltage		Viso	5000	V rms
Operating Temperature		Topr	-55~+110	°C
Storage Temperature		Tstg	-55~+125	°C
*2 Soldering Temperature		Tsol	260	°C

^{*1} AC for 1 minute, R.H= 40~ 60%RH

- -Isolation voltage shall be measured using the following method.
 - (1) Short between anode and cathode on the primary side and between collector, emitter and base on the secondary side.
 - (2) The isolation voltage tester with zero-cross circuit shall be used.
 - (3) The waveform of applied voltage shall be a sine wave

^{*2} For 10 seconds



Electro-Optical Characteristics

(Ta=25°C)

Electro-Optical Characteristics (1a-25 C)					20 (3)		
Parameter		Symbol	Min.	Тур.	Max.	Unit	Condition
	Forward	V_{F}	-	1.2	1.4	V	I _F =20mA
Input	Reverse Current	I_R	-	-	10	uA	V _R =4V
	Terminal	Ct	-	30	250	pF	V=0,f=1kHz
Output	Collector Dark current	I_{CEO}	-	-	100	nA	V _{CE} =20V
	Collector- Emitter breakdown voltage	$\mathrm{BV}_{\mathrm{CEO}}$	35	-	-	V	Ic=0.1mA
Transfer Characteristics	Current Transfer ratio	CTR	50	-	600	%	I _F =5mA ,V _{CE} =5V
	Collector- Emitter saturation voltage	V _{CE(sat)}	-	0.1	0.2	V	I _F =20mA ,Ic=1 mA
	Isolation resistance	R _{ISO}	5×10 ¹⁰	10 ¹¹	-	Ω	DC500V,40~60%R.H
	Flotation capacitance	Cf	-	0.6	1.0	pF	V=0, f=1MHz
	Cut-off frequency	fc	-	80	-	kHz	V_{CE} =5V, I_{C} =2 mA R_{L} =100 Ω , -3dB
	Rise time	$t_{\rm r}$	-	4	18	us	V _{CE} =2V
	Fall time	t_{f}	-	3	18	us	$I_C=2mA,R_L=100\Omega$



Supplement

Current Transfer Ratio CTR

Current Transfer Ratio CTR							
Sub-Model No.	Rank mark	CTR (%)	Condition				
EL817* note 1		50 to 600					
EL817* (L) note2	L	50 to 100					
EL817* (A)	A	80 to 160					
EL817* (B)	В	130 to 260	$I_F = 5 \text{ mA}$				
EL817* (C)	С	200 to 400	$V_{CE} = 5 \text{ V}$				
EL817* (D)	D	300 to 600	$T_a = 25^{\circ}C$				
EL817* (AB)	A or B	80 to 260					
EL817* (BC)	B or C	130 to 400					
EL817* (CD)	C or D	200 to 600					

Note1. The symbol "* " can be none or S or M by different leads form request

Note2. The symbol "()" can be CTR rank

Fig. 1 Forward Current vs.

Ambient Temperature

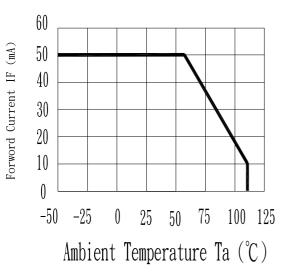
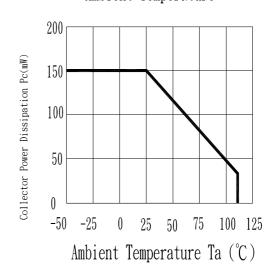


Fig. 2 Collecter Power Dissipation vs.
Ambient Temperature

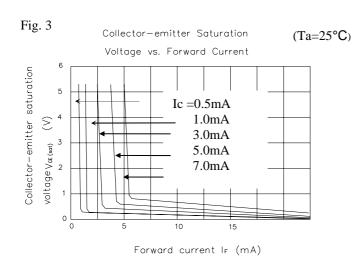




Forward current I _{mA)

Relative current ratio (%)

EL817 Series Technical Data Sheet Photocoupler-RoHS Compliant



Forward Current vs. Forward Voltage Fig.5 Voltage

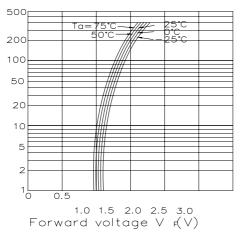
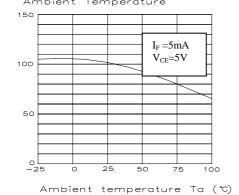
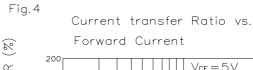
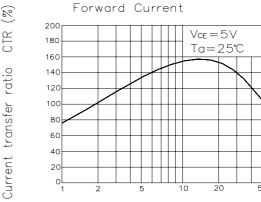


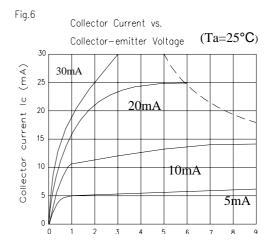
Fig.7 Relative Current Transfeer Ratio vs. Ambient Temperature



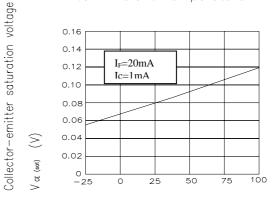




Forward current IF (mA)

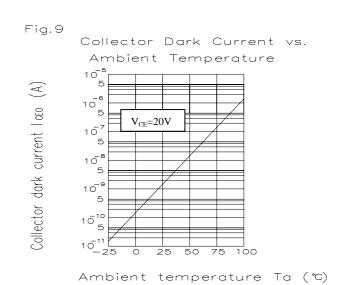


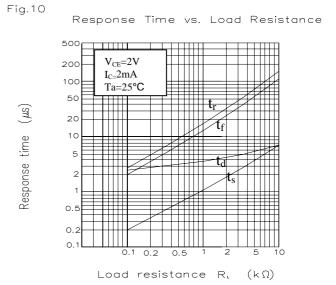
Collector-emitter Saturation Voltage vs. Ambient Temperature

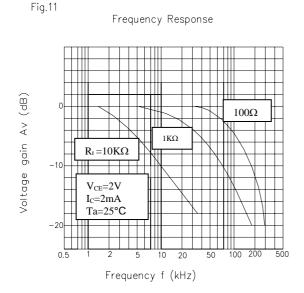


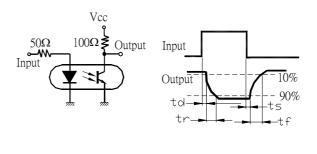
Ambient temperature Ta (℃)













RELIABILITY PLAN

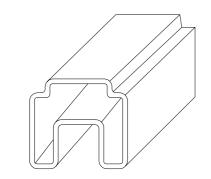
• The reliability of products shall be satisfied with items listed below.

Confidence level: 90 %, LTPD: 10 %

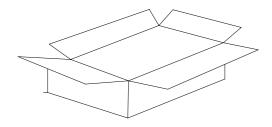
Classification	Test Item	Description & Condition	(Acc.) Sample	Failure Criteria	Reference Standard
Endurance test	Operation Life *	$Ta = 25 \pm 3^{\circ}C$ $IR: If = 50 \text{ mA}$ $Pt: Pc = 130 \text{ mW (Vf=1.4v)}, 1000 \text{ hrs}$	0 / 22		MIL-S-750 : 1026 MIL-S-883 : 1005 JIS C 7021 : B-1
	High Temperature / High Humidity Reverse Bias (H3TRB)	Ta = 85 ± 3°C , Humi. = 85 % rh Pt: 80% * Vce (max rating) , 1000 hrs	0 / 22	CTR shift > 1.2 Vf > U* 1.0 Ir > U * 1.0 Vce(sat) > U*1.0	JIS C 7021 : B-11
	High Temperature Reverse Bias (HTRB)	Ta = 105 ± 3°C Pt: 100% * Vce (Max rating) , 1000 hrs	0 / 22	Bvceo < L*1.0 Bveco < L*1.0	JIS C 7021 : B-8
	Low Temperature Storage	$Ta = -50 \pm 3^{\circ}C$, 1000 hrs	0 / 22		JIS C 7021 : B-12
	High Temperature Storage	$Ta = 125 \pm 3^{\circ}C$, 1000 hrs	0 / 22	L :Low Spec.Limit	JIS C 7021 : B-10 MIL-S-883 : 1008
	Auto clave	P = 15 PSIG , Ta = 121 °C , Humi. = 100 % rh , 48 hrs	0 / 22	U : Up Spec.	JESD 22-A102-B
Environmental	Temperature Cycling	125°C ~ - 55 °C	0 / 22	Limit	MIL-S-883 :1010
Test	(Air to Air)	30 ~ 30 min , 100 cycles			JIS C 7021 : A-4
	Thermal Shock	125 ~ - 55°C	0 / 22		MIL-S-202 : 107D
	(Liquid to Liquid)	t (dwell) = 5 min t (trans.) = 10 sec , 100 cycles			MIL-S-750 : 1051 MIL-S-883 :1011
	Solder Resistance	$Ta = 260 \pm 3^{\circ}C$ $t \text{ (dwell)} = 10 \pm 1 \text{ sec}$	0 / 22		MIL-S-750 : 2031 JIS C 7021 : A-1
	Solder Ability	$Ta = 230 \pm 3 \text{ °C}$ $t \text{ (dwell)} = 5 \pm 1 \text{ sec}$	0 / 22		MIL-S-883 : 2003 JIS C 7021 : A-2



- 1. Tube Packing Specifications (For Dip & M Type)
 - 1. Tube



2. Inner Carton

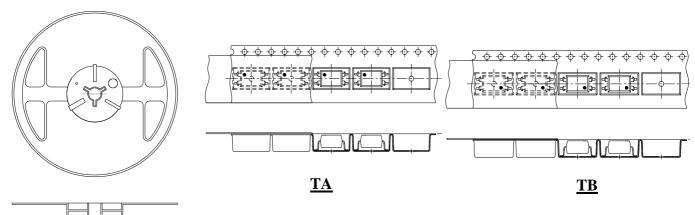


- Packing Quantity
 - 1. 100 Pcs/ Per Tube
 - 2. 25 Tubes / Inner Carton
 - 3. 12 Inner Cartons / Outside Carton

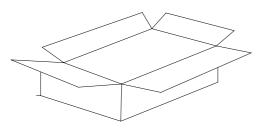


1. Tape & Reel Packing Specifications

1. Tape & Reel (For S & S1 Type only)



2. Inner Carton



Packing Quantity

- 1. 1,000 Pcs / Per Reel
- 2. 3 Reels / Inner Carton
- 3. 10 Inner Cartons / Outside Carton